

Ordering number:EN3291



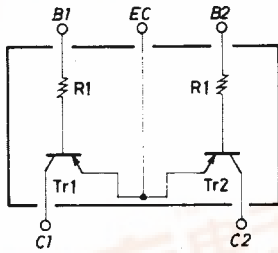
FC137

PNP Epitaxial Planar Silicon Composite Transistor Switching Applications (with Bias Resistance)

Features

- On-chip bias resistances ($R1=4.7k\Omega$).
- Composite type with 2 transistors contained in the CP package currently in use, improving the mounting efficiency greatly.
- The FC137 is formed with two chips, being equivalent to the 2SA1510, placed in one package.
- Excellent in thermal equilibrium and pair capability.

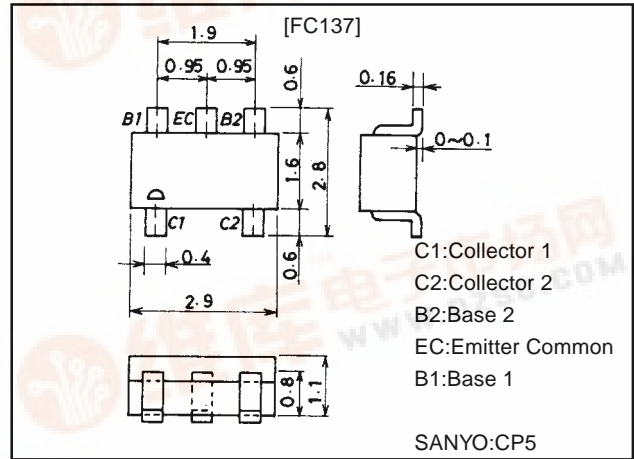
Electrical Connection



Package Dimensions

unit:mm

2066



Specifications

Absolute Maximum Ratings at $T_a = 25^\circ C$

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V_{CBO}		-50	V
Collector-to-Emitter Voltage	V_{CEO}		-50	V
Emitter-to-Base Voltage	V_{EBO}		-5	V
Collector Current	I_C		-100	mA
Peak Collector Current	I_{CP}		-200	mA
Collector Dissipation	P_C	1 unit	200	mW
Total Power Dissipation	P_T		300	mW
Junction Temperature	T_J		150	$^\circ C$
Storage Temperature	T_{stg}		-55 to +150	$^\circ C$

Electrical Characteristics at $T_a = 25^\circ C$

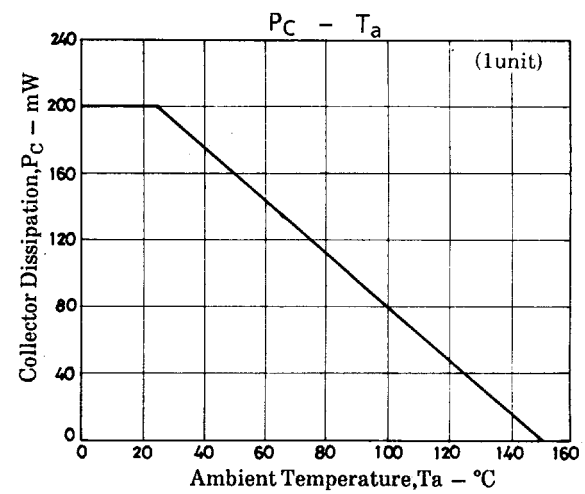
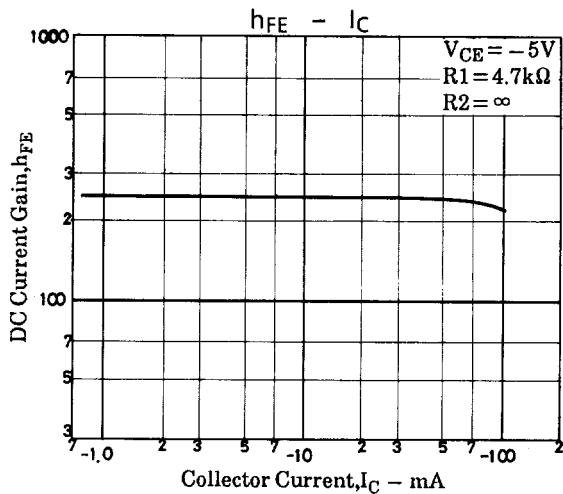
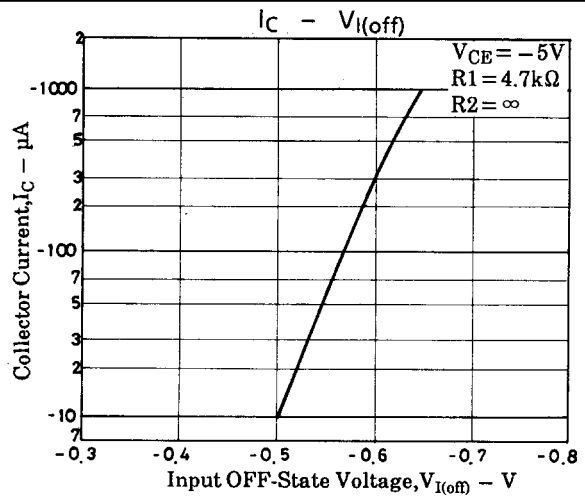
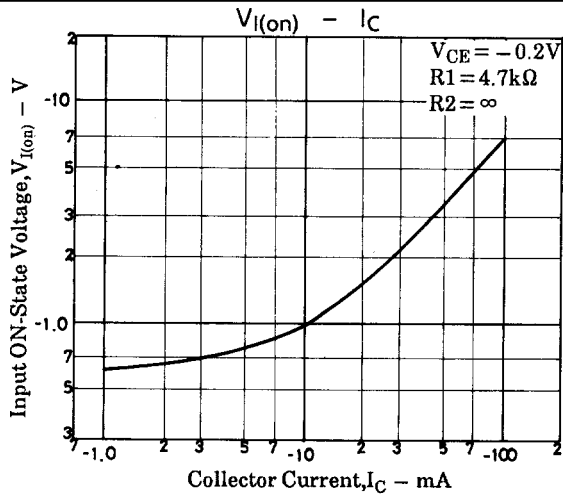
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I_{CBO}	$V_{CB}=-40V, I_E=0$			-0.1	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=-5V, I_C=0$			-0.1	μA
DC Current Gain	h_{FE}	$V_{CE}=-5V, I_C=-10mA$	100			
Gain-Bandwidth Product	f_T	$V_{CE}=-10V, I_C=-5mA$		200		MHz
Output Capacitance	C_{ob}	$V_{CB}=-10V, f=1MHz$		5.1		pF
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C=-10mA, I_B=-0.5mA$		-0.1	-0.3	V
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C=-10\mu A, I_E=0$	-50			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C=-100\mu A, R_{BE}=\infty$	-50			V
Input OFF-State Voltage	$V_{I(off)}$	$V_{CE}=-5V, I_C=-100\mu A$	-0.4	-0.55	-0.8	V
Input ON-State Voltage	$V_{I(on)}$	$V_{CE}=-0.2V, I_C=-10mA$	-0.6	-1.0	-2.0	V
Input Resistance	$R1$		3.3	4.7	6.1	k Ω

Note:The specifications shown above are for each individual transistor.

Marking:137



FC137



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